Crystals for applications in a muon collider



Outlook

• Brief introduction

- Tungsten crystals for coherent pair production
- Innovative sources of hard radiation
- Conclusions

Crystals technology at INFN











Collimation Beam steering
Beam steering Innovative radiation sources
Innovative radiation sources Pair production studies
Pair production studies
Innovative detectors

Beam steering
Innovative radiation sources
Pair production studies

CRYSBEAM SELDOM

INFN Competencies

INFN has competencies related to

- Development of innovative ideas and research activities (connected to channeling and related effects)
- Crystals manufacturing and characterization
- Holders manufacturing and characterization
- Goniometry
- Trackers and detectors
- Data analysis
- Design of setups for channeling experiments

INFN is a scientific agency encompassing a full set of competencies related to studies of coherent effects between charged particle beams and crystals.

INFN infrastructure

Laboratory fully equipped for silicon micro and nanomachining ISO₄ certified clean room (130 m²)

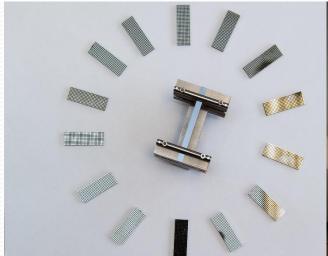
High-resolution x-ray diffraction
Dicing and polishing equipment
White light and Fizeau inteferferometers



INFN infrastructure

Laboratory fully equipped for silicon micro and nanomachining

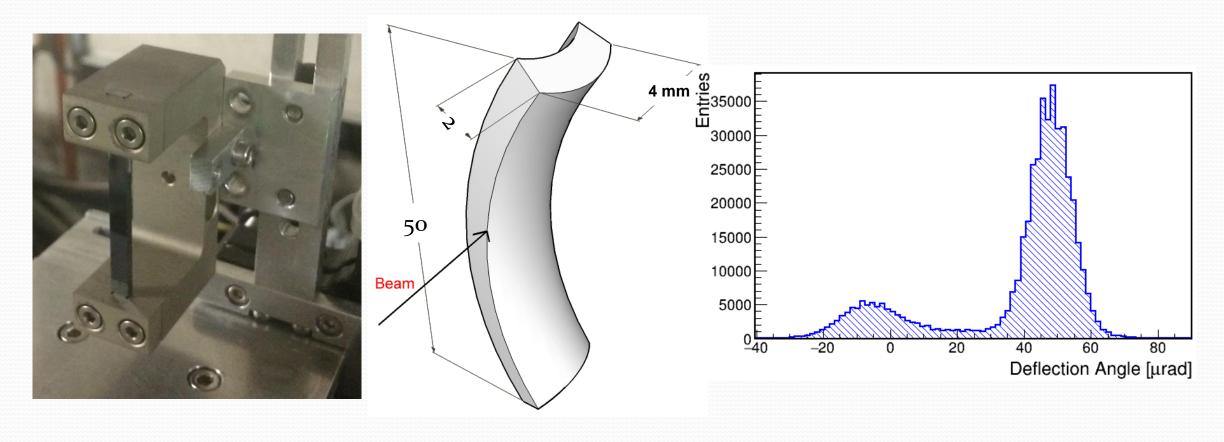
Fotolitography
Equipment for silicon chemical etching
Nanoimpringing







Strip crystals for the LHC

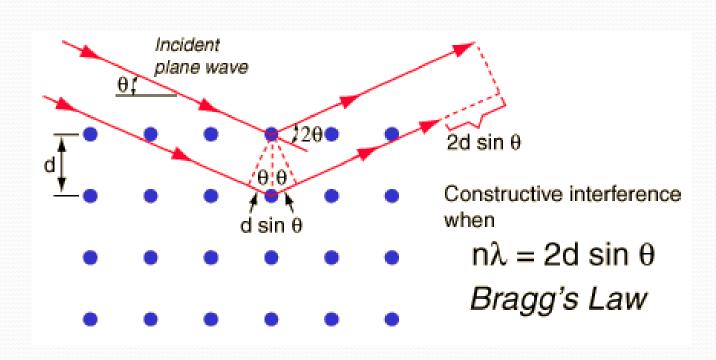


A primary bending is mechanically imposed along the 50 mm size. As a result, «anticlastic bending» manifests along the 4 mm size.

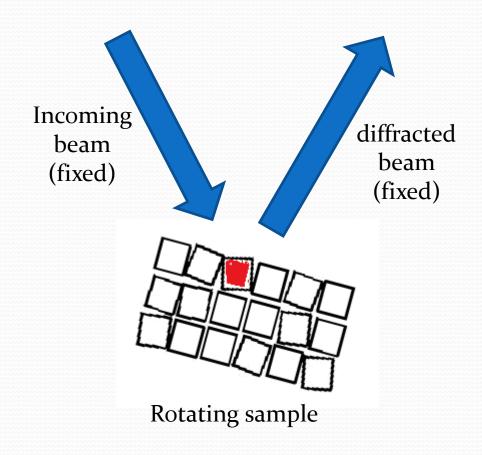
Tungsten crystals for coherent pair production

- Tungsten crystals for intense radiation generation for hybrid positron source and pair production (KLEVER)
- Innovative sources of hard radiation
- Conclusions

Tungsten crystals for coherent pair production X-rays diffraction



Rocking Curve



Tungsten crystals for coherent pair production Instrument set-up

- Synchrotron Beamline Bo₅ @ ESRF in Grenoble
 - 6→60 KeV x-rays
 - High intensity and quality of beam (only 4 other synchrotrons worldwide with similar features in term of design and power)!!
 - High resolution imaging detectors (~5 μ m vertical, 5 μ m/sin θ_B horizontal)
- High resolution X-rays diffractometer (HRXRD) @ INFN-Ferrara
 - 8.14 KeV x-rays (Cu Kα₁)
 - Analysis of diffracted beam angular divergence (triple-axis configuration)
 - Mapping of total angular distribution of domains in different part of the sample

Sample W_ID12 surface (111) → diffract (222), Bragg angle 19.3 degree at 20keV

Perfect

~10 µrad

6000

1000

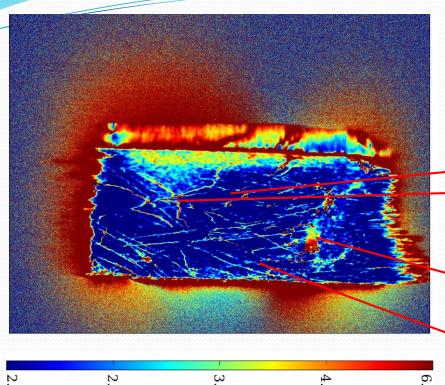
-0.2

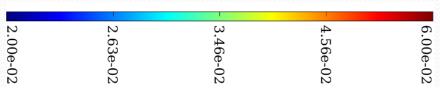
-0.1

0.1

Angle ω (degress), ref. at 19.9265 degrees

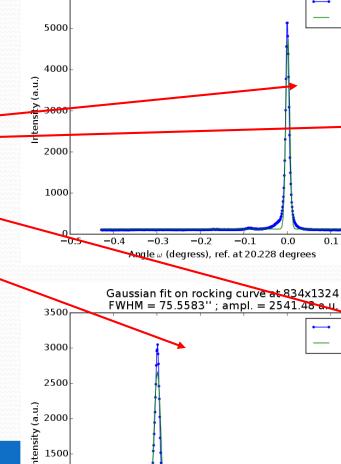
0.2



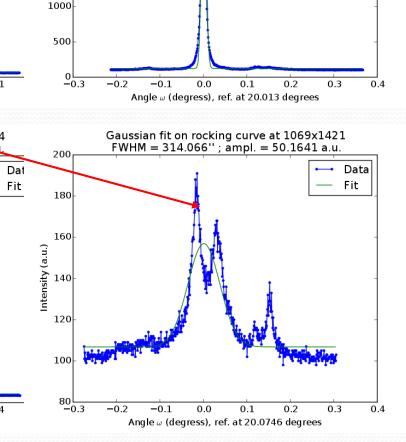


Blue good	Blue	Yellow	Red
185 µrad	209 µrad	366.5 µrad	1522.5 µrad

Courtesy of R. Camattari



Gaussian fit on rocking curve at 1025x1550 FWHM = 38.0878"; ampl. = 4720.9 a.u.



Gaussian fit on rocking curve at 948x1515 FWHM = 43.1002"; ampl. = 3079.58 a.u.

Data

Fit

3500

3000

2500

(in 2000

Dat

Fit

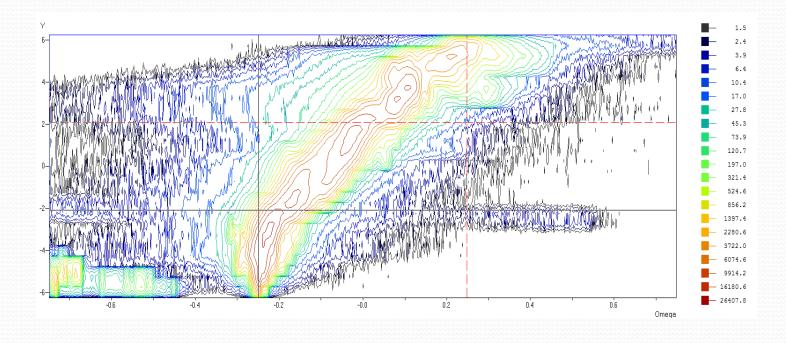
Tungsten crystals for test beam @ DESY

Reflection is observed at all points of the sample

The total angular distribution of all the crystals domains on all the crystal surface is roughly within 0.4° (7 mrad)

The angular spread of such domain is of the order of 1.5 mrad

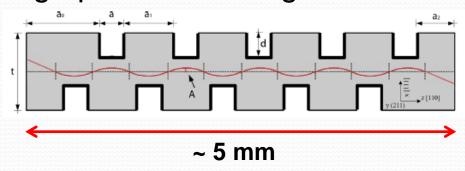
The angular position of the diffracted beam and its divergence is close to nominal, possible stress of the order of tens of Mpa.



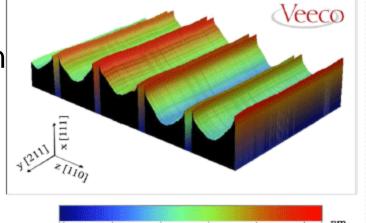
CRYSTALLINE UNDULATOR

- MANUFACTURING AND CHARACTERIZATIONS -

Crystalline undulator manufactured grooving a silicon substrate by means of a high precision dicing machine.



A periodical deformation is Imparted to the crystal Interferometric characterization (Veeco)

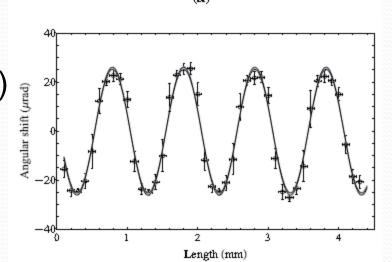


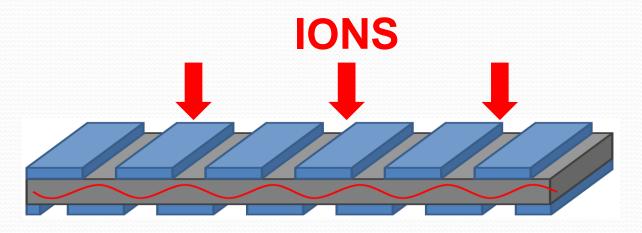
-5.0

11.8

-10.0

Characterization
@ ESRF (BM-05)

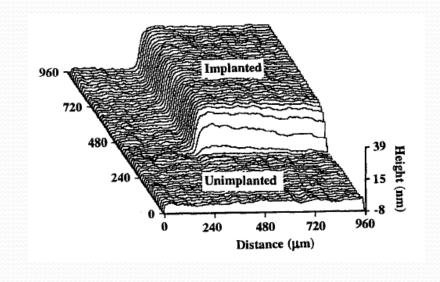




From <u>swelling</u> studies, a density reduction of 3.1% for the pure amorphous Si with respect to crystalline Si was found [1]. The grow of volume of the amorphized region transfers coactive forces to the crystal bulk, thus producing an elastic strain field within the crystal, which results in a net curvature within the crystal bulk.

advantages: no delamination or crack propagation

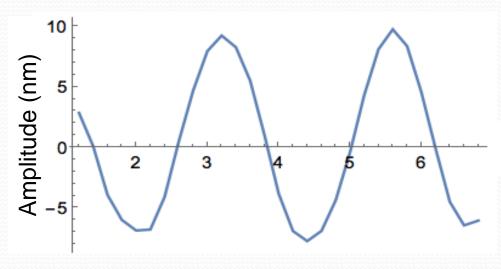
Omogeneus flux of lons (He, Ar) impinges on the free surface of the wafer creating damages and so an amorphization of the crystalline structure.



[1] P. K. Giri at al., Phis. Rev. B 65, 012110 (2001)

CRYSTALLINE UNDULATOR

- MANUFACTURING AND CHARACTERIZATIONS



Transverse position (mm)

- Implanted ions: 15 KeV
 He⁺⁺
- Crystal deformation characterized at DIGRA (ILL) by means of highly energetic gamma-rays
- 181 KeV photons
- Crystal exhibit a clear periodical deformation

Conclusions

 INFN is a scientific agency with a full set of capabilities and an international network of partners capable to perfom experiments aimed to study coherent interactions between charged particle beams and crystals

 R&D on tungsten crystals already started, in collaboration with ELIOT and KLEVER experiments

Prototypes of crystalline undulators ready